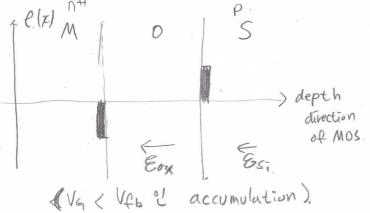
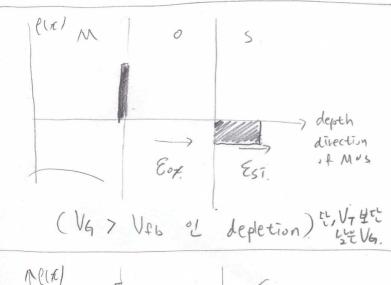
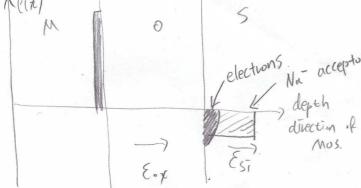
1. 作刊 MOS Capacitor 子至时代 gate 1. (大) M 对 Tob It MOS Capacitor 子至时代 gate 1. (大) M 对 Tob It Substrate 告记了什么 Coumulation, depletion, threshold, in version 学证中的 Charge distribution党 对于 牙上如 生门 - 下上, Substrate 上 P-type doping 子社会 7. 26台上,

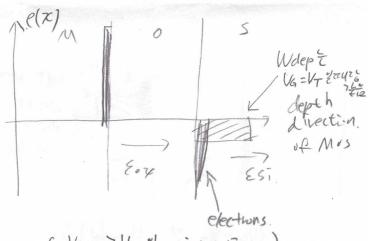


VG = VAB 2 zey flot band 2t. Charge distribution X.





(Vg=VT of threshold)



CVG 7V72 inversion)

2. 1th ZEON CHEU Substrate doping 3 tol

N-type 2 78701 CHI FIRM HILL.

PHO D S

Appech

Appec

charge distribution X

depth

direction

of M

of S

pletion) th, V7 4th

pletion) the V7 4th

Est V6.

Claretion

Est V6.

Charge distribution X

depth

direction

Est V6.

Litt V6.

V7 (VG (VFb. of depletion.)

Litt depth

VG = Vfb 2 and floor bund 2L

